

TOSHIBA

RN2112F, RN2113F

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

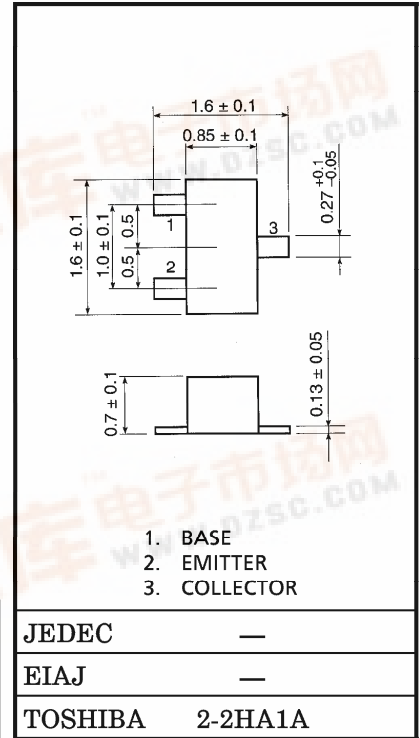
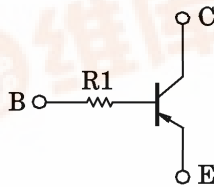
RN2112F, RN2113F

SWITCHING, INVERTER CIRCUIT, INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATIONS.

Unit in mm

- With Built-in Bias Resistors
- Simplify Circuit Design
- Reduce a Quantity of Parts and Manufacturing Process
- Complementary to RN1112F, RN1113F

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta = 25°C)

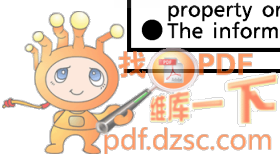
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-100	mA
Collector Power Dissipation	P _C	100	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

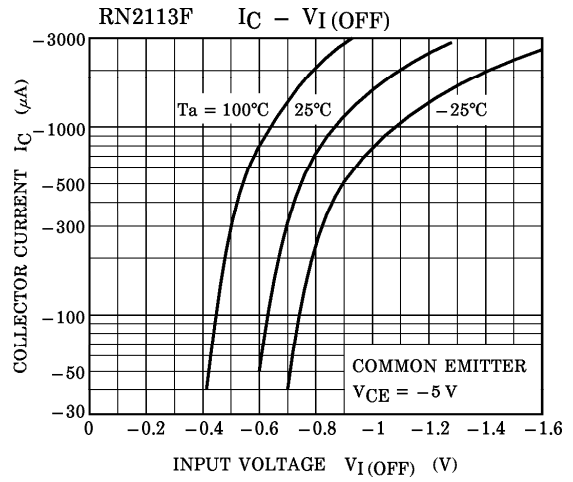
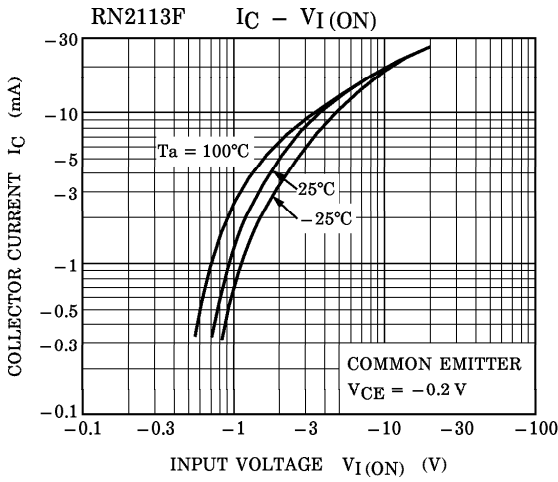
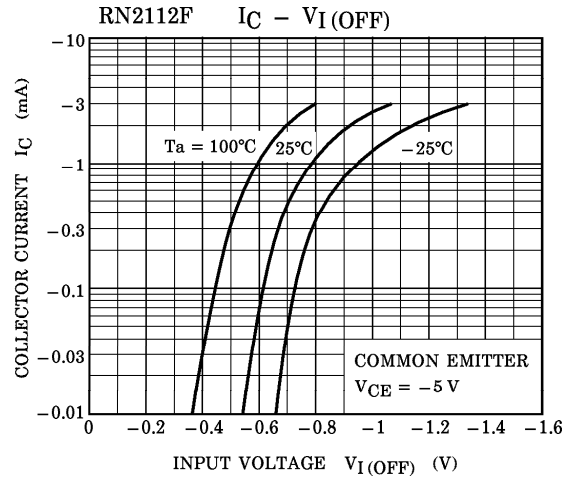
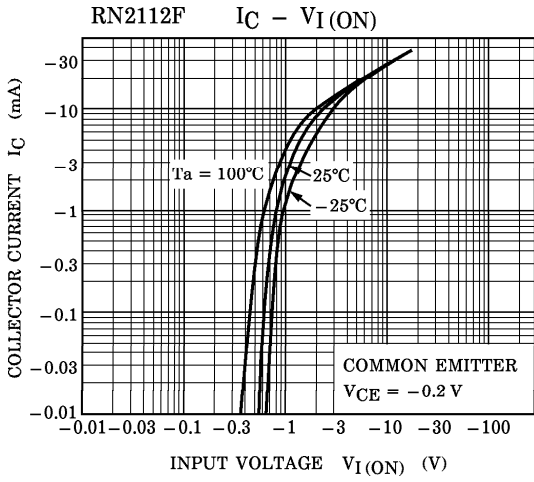
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

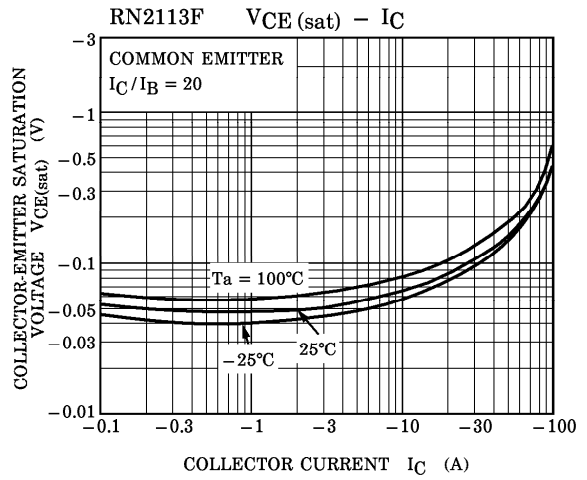
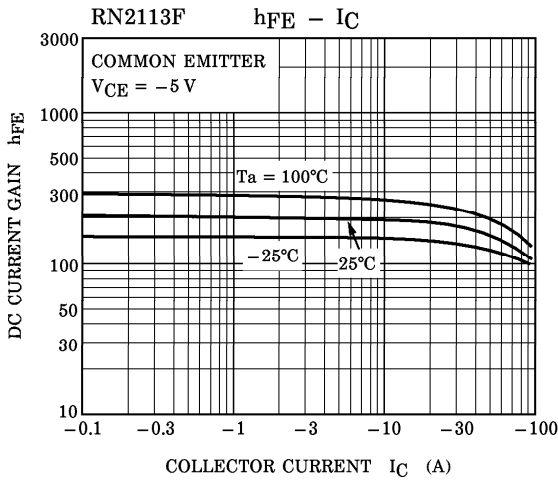
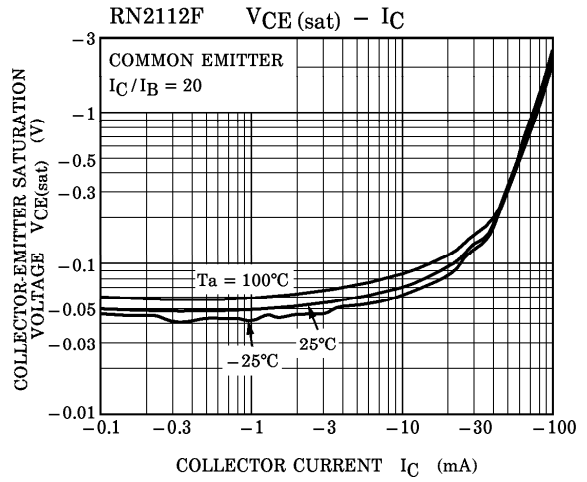
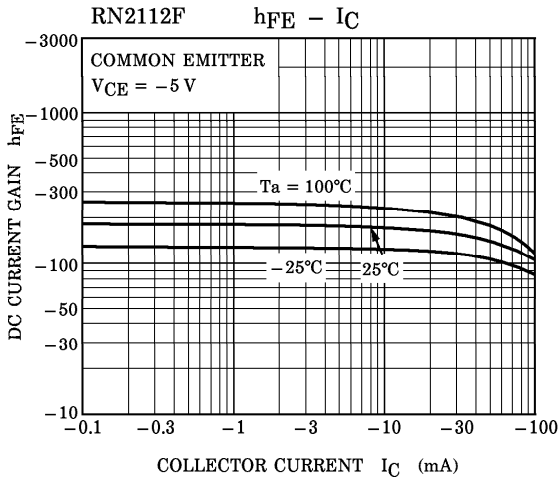
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I _{CBO}	V _{CB} = -50 V, I _E = 0	—	—	-100	nA	
Emitter Cut-off Current	I _{EBO}	V _{EB} = -5 V, I _C = 0	—	—	-100	nA	
DC Current Gain	h _{FE}	V _{CE} = -5 V, I _C = -1 mA	120	—	400		
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C = -5 mA, I _B = -0.25 mA	—	-0.1	-0.3	V	
Transition Frequency	f _T	V _{CE} = -10 V, I _C = -5 mA	—	200	—	MHz	
Collector Output Capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	—	3	6	pF	
Input Resistor	RN2112F	R1	—	15.4	22	28.6	kΩ
	RN2113F			32.9	47	61.1	

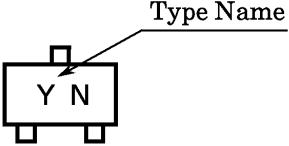
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TYPE NAME	MARKING
RN2112F	
RN2113F	